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[54] TUNGSTEN SILICIDE (WSI_x) DEPOSITION PROCESS FOR SEMICONDUCTOR MANUFACTURE

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[57]

ABSTRACT

A semiconductor manufacturing process for depositing a tungsten silicide film on a substrate includes deposition of a tungsten silicide nucleation layer on the substrate using a (CVD) process with a silane source gas followed by deposition of the tungsten silicide film with a dichlorosilane source gas. This two step process allows dichlorosilane to be used as a silicon source gas for depositing a tungsten silicide film at a lower temperature than would otherwise be possible and without plasma enhancement. Tungsten silicide films deposited by this process are characterized by low impurities, good step coverage, and low stress with the silicon substrate.

15 Claims, 1 Drawing Sheet

DEPOSITING A NUCLEATION LAYER OF TUNGSTEN SILICIDE (WSix) ON A SUBSTRATE USING A (CVD) PROCESS WITH SILANE (SiH₄) AS A SILICON SOURCE GAS.

10

DEPOSITING A TUNGSTEN SILICIDE (WSix) FILM ON THE NUCLEATION LAYER USING A (CVD) PROCESS WITH DICHLOROSILANE AS A SILICON SOURCE GAS.

12